

EAST: [10772260 gate insul with H O metal wsp:1]
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- S22: (3) S28 S21
- S23: (297191) (metal film) near2 (silicon) S1
- S24: (458) metal near2 (n nitrogen) near2 bond\$4
- S25: (0) S22 and S24
- S26: (250348) amorphous
- S27: (20) S23 same S24
- S28: (137) S23 and S24
- S30: (48) S28 and S26
- S29: (3) S24 with S26
- S31: (8) S22 S29
- S32: (1432422) bond\$4
- S33: (4) S31 and S32
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- S35: (3) S24 with S26
- S36: (6) S24 same S26
- S37: (0) S38 and S23
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- S40: (842704) gate
- S41: (8866) S23 same S40
- S42: (13) S39 and S41

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|----|--------------------------|--------------|-----------------|--------|----|--|---------|------------|-----------|--------------------------|--------------------------|--------------------------|--------------------------|-----------|-----|
| 1 | <input type="checkbox"/> | Pomareda, US | 2004014701A | 2004 | 16 | Surface preparation prior to depositio | 438/59 | 257/E21.19 | | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | BS 200401 | |
| 2 | <input type="checkbox"/> | Koyama, M | US 20020149065 | 2002 | 2 | MIS field effect transistor and method | 257/36 | 257/333 | | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 200201 | |
| 3 | <input type="checkbox"/> | Pomareda, US | 20040121620 | 2004 | 16 | Surface preparation prior to depositio | 438/78 | 257/E21.19 | | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 200401 | |
| 4 | <input type="checkbox"/> | Koyama, M | US 2003021719 A | 2003 | 2 | MIS field effect transistor and method | 438/59 | 257/411 | | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 20030 | |
| 5 | <input type="checkbox"/> | Baum, Tho | US 20020187644 | 2002 | 2 | Source reagent compositions for CVD f | 438/70 | 257/E21.27 | | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 200201 | |
| 6 | <input type="checkbox"/> | Baum, Tho | US 20020175393 | 2002 | 2 | Source reagent compositions for CVD f | 257/50 | 257/E21.27 | | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 200201 | |
| 7 | <input type="checkbox"/> | Pomareda, US | 20020098627 | 2002 | 16 | Surface preparation prior to depositio | 438/14 | 257/E21.19 | | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 20020 | |
| 8 | <input type="checkbox"/> | Baum, Tho | US 6868638 B2 | 2005 | 2 | Source reagent compositions for CVD f | 427/12 | 427/255.3 | | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 68686 | |
| 9 | <input type="checkbox"/> | Koyama, M | US 6808635 B2 | 2004 | 2 | MIS field effect transistor with metal o | 257/411 | 257/406 | | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 68086 | |
| 10 | <input type="checkbox"/> | Pomareda, US | 6613895 B2 | 2003 | 16 | Surface preparation prior to depositio | 438/78 | 257/E21.19 | | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 661389 | |

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